

Inchange Semiconductor

Product Specification

Silicon PNP Power Transistors

MJ15027

DESCRIPTION

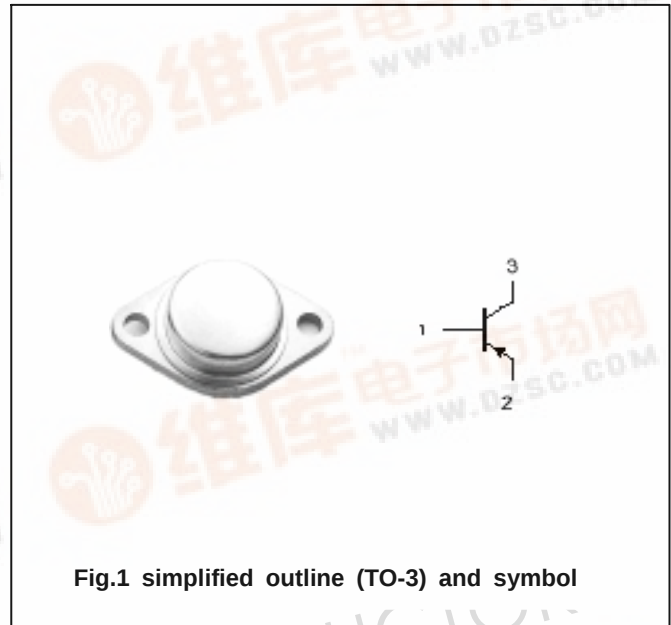
- With TO-3 package
- Complement to type MJ15026
- Excellent safe operating area

APPLICATIONS

- For high power audio ,stepping motor and other linear applications
- Relay or solenoid drivers
- DC-DC converters inverters

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-200	V
V_{CEO}	Collector-emitter voltage	Open base	-200	V
V_{EBO}	Emitter-base voltage	Open collector	-7	V
I_C	Collector current		-15	A
I_B	Base current		-7	A
P_C	Collector power dissipation	$T_C=25$	250	W
T_j	Junction temperature		175	
T_{stg}	Storage temperature		-65~175	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal resistance junction to case	0.98	/W

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-50mA ; I _B =0	-200			V
V _{EBO}	Emitter-base breakdown voltage	I _E =-1mA ; I _C =0	-7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-10A; I _B =-1A			-2.0	V
V _{BE}	Base-emitter on voltage	I _C =-5A ; V _{CE} =-5V			-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-200V; I _E =0			-0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-7V; I _C =0			-0.1	mA
h _{FE}	DC current gain	I _C =-5A ; V _{CE} =-5V	25		150	
f _T	Transition frequency	I _C =-0.5A ; V _{CE} =-12V	15			MHz

固电半导体
INCHANGE SEMICONDUCTOR

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PACKAGE OUTLINE

